

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

# 2SC4682

Strobe Flash Applications

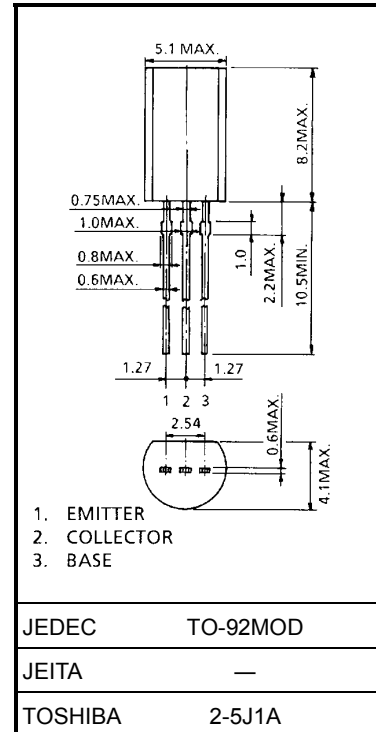
Medium Power Amplifier Applications

Unit: mm

- Excellent hFE linearity:  $h_{FE} (1) = 800$  to  $3200$  ( $V_{CE} = 1$  V,  $I_C = 0.5$  A)  
 $h_{FE} (2) = 500$  (typ.) ( $V_{CE} = 1$  V,  $I_C = 3$  A)
- Low saturation voltage:  $V_{CE} (sat) = 0.5$  V (max)  
 $(I_C = 3$  A,  $I_B = 30$  mA)

### Maximum Ratings (Ta = 25°C)

| Characteristics             |       | Symbol        | Rating     | Unit |
|-----------------------------|-------|---------------|------------|------|
| Collector-base voltage      |       | $V_{CBO}$     | 30         | V    |
| Collector-emitter voltage   |       | $V_{CES}$     | 30         | V    |
|                             |       | $V_{(BR)CEO}$ | 15         |      |
| Emitter-base voltage        |       | $V_{EBO}$     | 6          | V    |
| Collector current           | DC    | $I_C$         | 3          | A    |
|                             | Pulse | $I_{CP}$      | 6          |      |
| Base current                |       | $I_B$         | 0.8        | A    |
| Collector power dissipation |       | $P_C$         | 900        | mW   |
| Junction temperature        |       | $T_j$         | 150        | °C   |
| Storage temperature range   |       | $T_{stg}$     | -55 to 150 | °C   |

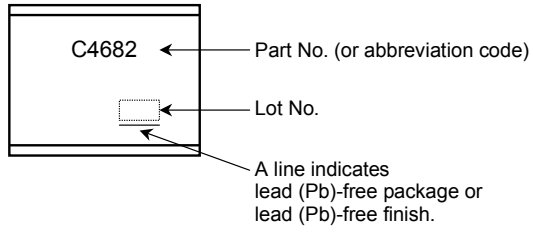


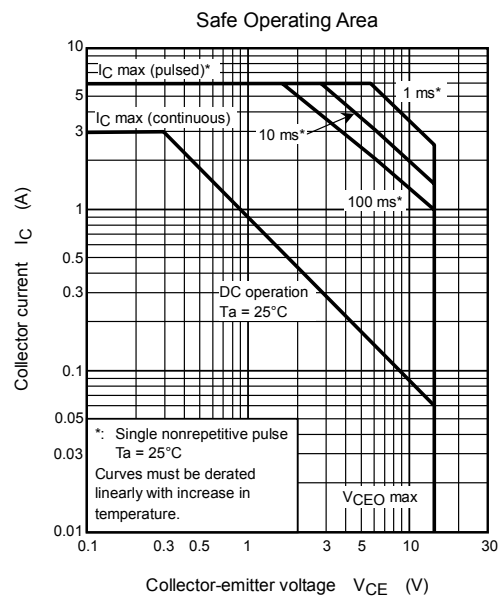
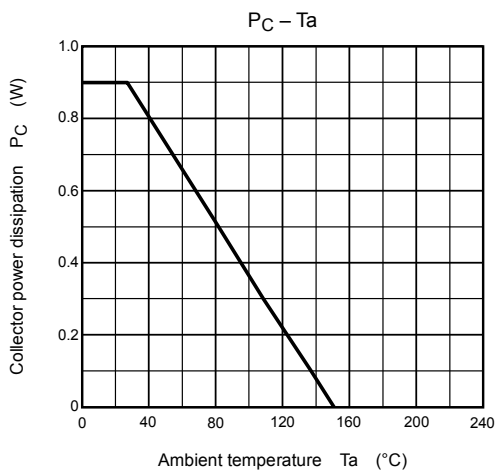
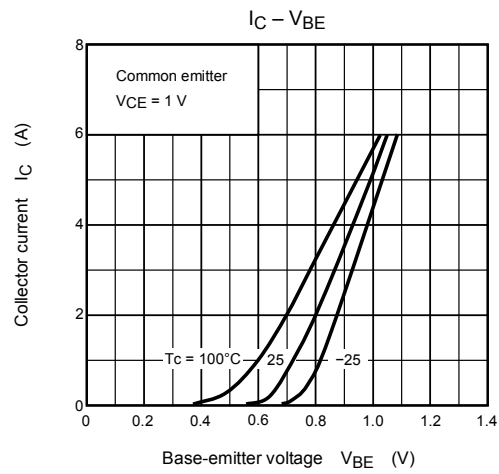
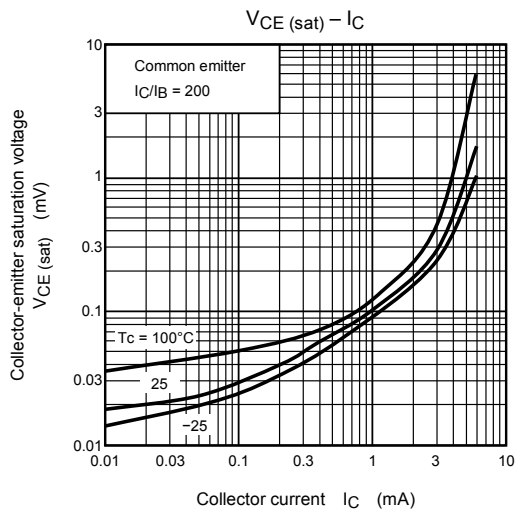
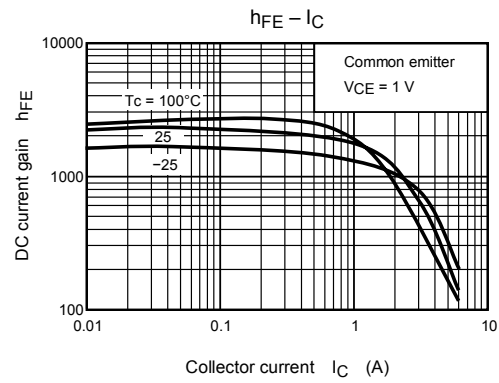
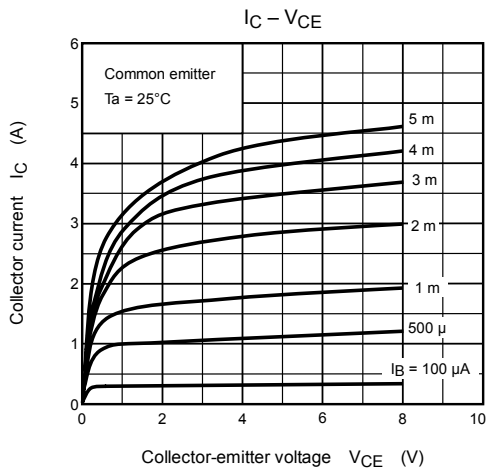
Weight: 0.36 g (typ.)

### Electrical Characteristics (Ta = 25°C)

| Characteristics                      | Symbol         | Test Condition                           | Min | Typ. | Max  | Unit |
|--------------------------------------|----------------|--|-----|------|------|------|
| Collector cut-off current            | $I_{CBO}$      | $V_{CB} = 30$ V, $I_E = 0$               | —   | —    | 1    | μA   |
| Emitter cut-off current              | $I_{EBO}$      | $V_{EB} = 6$ V, $I_C = 0$                | —   | —    | 10   | μA   |
| Collector-emitter breakdown voltage  | $V_{(BR)CEO}$  | $I_C = 10$ mA, $I_B = 0$                 | 15  | —    | —    | V    |
| DC current gain                      | $h_{FE} (1)$   | $V_{CE} = 1$ V, $I_C = 0.5$ A            | 800 | —    | 3200 |      |
|                                      | $h_{FE} (2)$   | $V_{CE} = 1$ V, $I_C = 3$ A              | 300 | 500  | —    |      |
| Collector-emitter saturation voltage | $V_{CE} (sat)$ | $I_C = 3$ A, $I_B = 30$ mA               | —   | 0.25 | 0.5  | V    |
| Base-emitter voltage                 | $V_{BE}$       | $V_{CE} = 1$ V, $I_C = 3$ A              | —   | 0.85 | 1.2  | V    |
| Transition frequency                 | $f_T$          | $V_{CE} = 1$ V, $I_C = 0.5$ A            | —   | 150  | —    | MHz  |
| Collector output capacitance         | $C_{ob}$       | $V_{CB} = 10$ V, $I_E = 0$ , $f = 1$ MHz | —   | 30   | —    | pF   |

## Marking





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